TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

POWER GaAs MMIC TMD0708-2

Features:

■ HIGH POWER

■ BROAD BAND INTERNALLY MATCHED

P1dB= 33 dBm at 7.1 to 8.5 GHz

HIGH GAIN

HERMETICALLY SEALED PACKAGE

 $G_{1dB}=22$ dB at 7.1 to 8.5 GHz

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	W	0. 1
FLANGE TEMPERATURE	Tf	$^{\circ}\!\mathbb{C}$	-30~+80
STORAGE TEMPERATURE	Tstg	$^{\circ}\!\mathbb{C}$	$-65\sim+175$

RF CHARACTERISTICS (Ta=25°C)

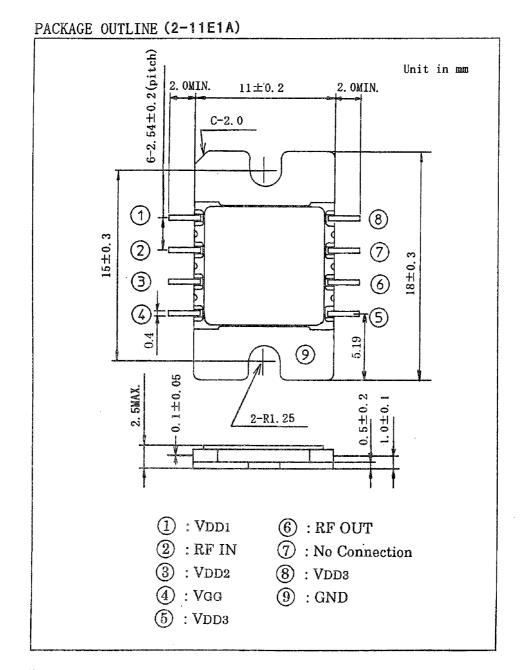
CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB	P1dB	VDD1=VDD2=VDD3=	dBm	32. 0	33. 0	_
Gain Compression Point		10V,				
Power Gain at 1 dB	G1dB	VGG=-5 V	dB	20.0	22. 0	_
Gain Compression Point		f= 7.1-8.5 GHz				
Drain Current	IDD *		A	1	1.70	2.00
Input VSWR	VSWRi			_	1	3. 0

^{*} IDD=IDD1+IDD2+IDD3

[★] The information contained herein may be changed without prior notice. It is therefore advisable to contact TOSHIBA before proceeding with the design of equipment incorporating this product.



[★] The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260%. Flanges of devices should be attached using screws and washers. Recommended torques are $0.18\text{-}0.20~\text{N}\cdot\text{m}$.